

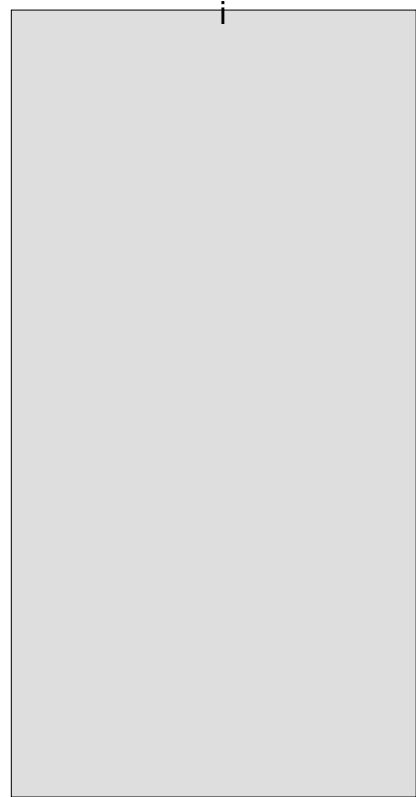


**JCT1225F 25A SCR**

Rev.A.1.1

**DESCRIPTION:**

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Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	5	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	20	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	1	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12V$ $R_L=33$	-	-	40	mA
$V_{GT}$		-	-	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	0.2	-	-	V
$I_L$	$I_G=1.2I_{GT}$	-	-	90	mA
$I_H$	$I_T=500mA$	-	-	80	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125$	1000	-	-	V/ $\mu s$
$t_{on}$	$I_G=50mA$ $I_A=500mA$ $I_R=50mA$ $T_j=25$	-	5	-	$\mu s$
$t_{off}$		-	70	-	

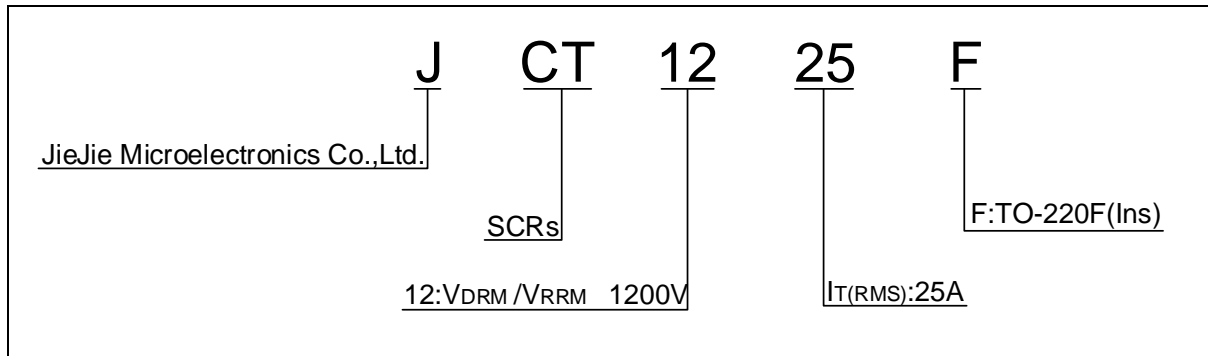
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=50A$ $t_p=380\mu s$	$T_j=25$	1.55	V
$V_{TO}$	Threshold voltage	$T_j=125$	0.74	V
$R_D$	Dynamic resistance	$T_j=125$	19	m
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	7	$\mu A$
$I_{RRM}$		$T_j=125$	2	mA

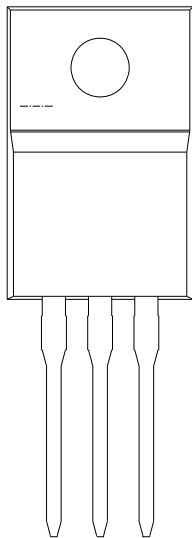
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(DC)	2.05	/W
$R_{th(j-a)}$	junction to ambient (DC)	60	/W

ORDERING INFORMATION



MARKING

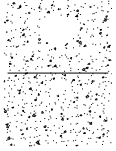









**PACKAGE MECHANICAL DATA**



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